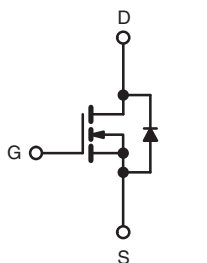
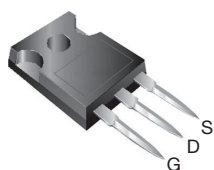


Power MOSFET

PRODUCT SUMMARY

V_{DS} (V)	900	
$R_{DS(on)}$ (Ω)	$V_{GS} = 10\text{ V}$	2.5
Q_g (Max.) (nC)	120	
Q_{gs} (nC)	16	
Q_{gd} (nC)	67	
Configuration	Single	

TO-247AC


N-Channel MOSFET

FEATURES

- Dynamic dV/dt Rating
- Repetitive Avalanche Rated
- Isolated Central Mounting Hole
- Fast Switching
- Ease of Paralleling
- Simple Drive Requirements
- Compliant to RoHS Directive 2002/95/EC



Available
RoHS*
COMPLIANT

DESCRIPTION

Third generation Power MOSFETs from Vishay provide the designer with the best combination of fast switching, ruggedized device design, low on-resistance and cost-effectiveness.

The TO-247AC package is preferred for commercial-industrial applications where higher power levels preclude the use of TO-220AB devices. The TO-247AC is similar but superior to the earlier TO-218 package because of its isolated mounting hole. It also provides greater creepage distance between pins to meet the requirements of most safety specifications.

ORDERING INFORMATION

Package	TO-247AC
Lead (Pb)-free	IRFPF40PbF
	SiHFPF40-E3
SnPb	IRFPF40
	SiHFPF40

ABSOLUTE MAXIMUM RATINGS ($T_C = 25^\circ\text{C}$, unless otherwise noted)

PARAMETER			SYMBOL	LIMIT	UNIT
Drain-Source Voltage			V _{DS}	900	V
Gate-Source Voltage			V _{GS}	± 20	
Continuous Drain Current	V _{GS} at 10 V	T _C = 25 °C	I _D	4.7	A
		T _C = 100 °C		2.9	
Pulsed Drain Current ^a			I _{DM}	19	
Linear Derating Factor				1.2	W/°C
Single Pulse Avalanche Energy ^b			E _{AS}	500	mJ
Repetitive Avalanche Current ^a			I _{AR}	4.7	A
Repetitive Avalanche Energy ^a			E _{AR}	15	mJ
Maximum Power Dissipation		T _C = 25 °C	P _D	150	W
Peak Diode Recovery dV/dt ^c			dV/dt	1.5	V/ns
Operating Junction and Storage Temperature Range			T _J , T _{stg}	- 55 to + 150	°C
Soldering Recommendations (Peak Temperature)		for 10 s		300 ^d	
Mounting Torque	6-32 or M3 screw			10	lbf · in
				1.1	N · m

Notes

- Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).
- $V_{DD} = 50\text{ V}$, starting $T_J = 25^\circ\text{C}$, $L = 42\text{ mH}$, $R_g = 25\ \Omega$, $I_{AS} = 4.7\text{ A}$ (see fig. 12).
- $I_{SD} \leq 4.7\text{ A}$, $dI/dt \leq 110\text{ A}/\mu\text{s}$, $V_{DD} \leq V_{DS}$, $T_J \leq 150^\circ\text{C}$.
- 1.6 mm from case.

* Pb containing terminations are not RoHS compliant, exemptions may apply

THERMAL RESISTANCE RATINGS

PARAMETER	SYMBOL	TYP.	MAX.	UNIT
Maximum Junction-to-Ambient	R_{thJA}	-	40	°C/W
Case-to-Sink, Flat, Greased Surface	R_{thCS}	0.24	-	
Maximum Junction-to-Case (Drain)	R_{thJC}	-	0.83	

SPECIFICATIONS ($T_J = 25\text{ }^{\circ}\text{C}$, unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static							
Drain-Source Breakdown Voltage	V _{DS}	V _{GS} = 0 V, I _D = 250 μA		900	-	-	V
V _{DS} Temperature Coefficient	ΔV _{DS} /T _J	Reference to 25 °C, I _D = 1 mA		-	1.0	-	V/°C
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250 μA		2.0	-	4.0	V
Gate-Source Leakage	I _{GSS}	V _{GS} = ± 20 V		-	-	± 100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 900 V, V _{GS} = 0 V		-	-	100	μA
		V _{DS} = 720 V, V _{GS} = 0 V, T _J = 125 °C		-	-	500	
Drain-Source On-State Resistance	R _{DS(on)}	V _{GS} = 10 V	I _D = 2.8 A ^b	-	-	2.5	Ω
Forward Transconductance	g _{fs}	V _{DS} = 50 V, I _D = 2.8 A ^b		2.5	-	-	S
Dynamic							
Input Capacitance	C _{iss}	V _{GS} = 0 V, V _{DS} = 25 V, f = 1.0 MHz, see fig. 5		-	1600	-	pF
Output Capacitance	C _{oss}			-	180	-	
Reverse Transfer Capacitance	C _{rss}			-	63	-	
Total Gate Charge	Q _g	V _{GS} = 10 V	I _D = 4.7 A, V _{DS} = 360 V, see fig. 6 and 13 ^b	-	-	120	nC
Gate-Source Charge	Q _{gs}			-	-	16	
Gate-Drain Charge	Q _{gd}			-	-	67	
Turn-On Delay Time	t _{d(on)}	V _{DD} = 450 V, I _D = 4.7 A , R _g = 9.1 Ω, R _D = 95 Ω, see fig. 10 ^b		-	15	-	ns
Rise Time	t _r			-	36	-	
Turn-Off Delay Time	t _{d(off)}			-	110	-	
Fall Time	t _f			-	32	-	
Internal Drain Inductance	L _D	Between lead, 6 mm (0.25") from package and center of die contact		-	5.0	-	nH
Internal Source Inductance	L _S			-	13	-	
Drain-Source Body Diode Characteristics							
Continuous Source-Drain Diode Current	I _S	MOSFET symbol showing the integral reverse p - n junction diode		-	-	4.7	A
Pulsed Diode Forward Current ^a	I _{SM}			-	-	19	
Body Diode Voltage	V _{SD}	T _J = 25 °C, I _S = 4.7 A, V _{GS} = 0 V ^b		-	-	1.8	V
Body Diode Reverse Recovery Time	t _{rr}	T _J = 25 °C, I _F = 4.7 A, dI/dt = 100 A/μs ^b		-	510	770	ns
Body Diode Reverse Recovery Charge	Q _{rr}			-	2.2	3.3	μC
Forward Turn-On Time	t _{on}	Intrinsic turn-on time is negligible (turn-on is dominated by L _S and L _D)					

Notes

- a. Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).
b. Pulse width $\leq 300\text{ }\mu\text{s}$; duty cycle $\leq 2\%$.

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

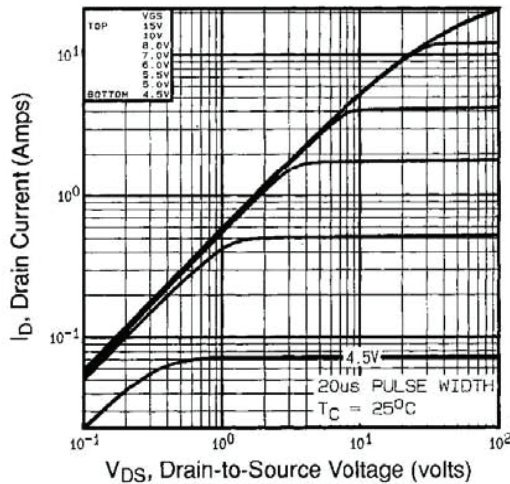


Fig. 1 - Typical Output Characteristics, $T_C = 25^\circ\text{C}$

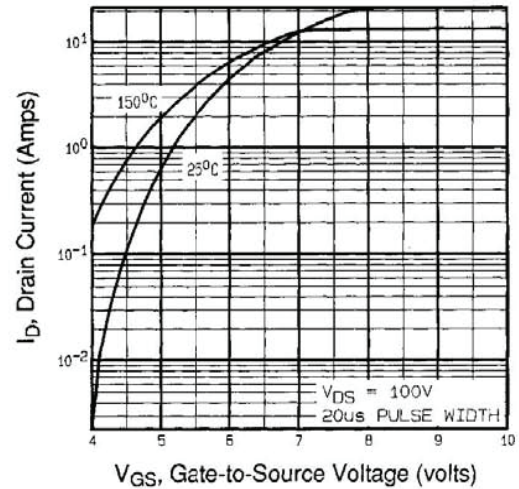


Fig. 3 - Typical Transfer Characteristics

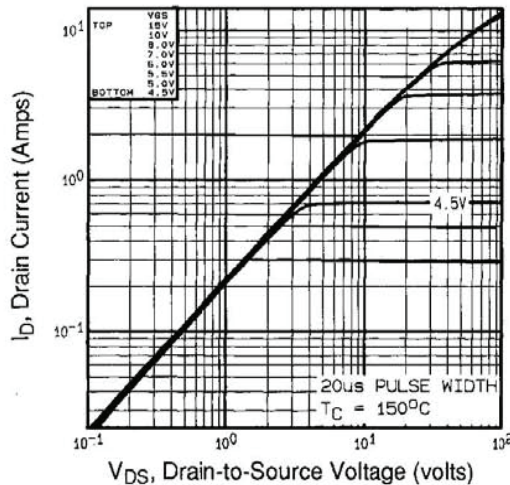


Fig. 2 - Typical Output Characteristics, $T_C = 150^\circ\text{C}$

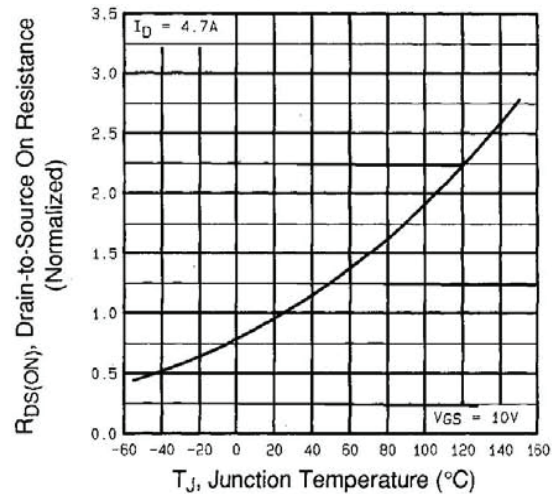


Fig. 4 - Normalized On-Resistance vs. Temperature

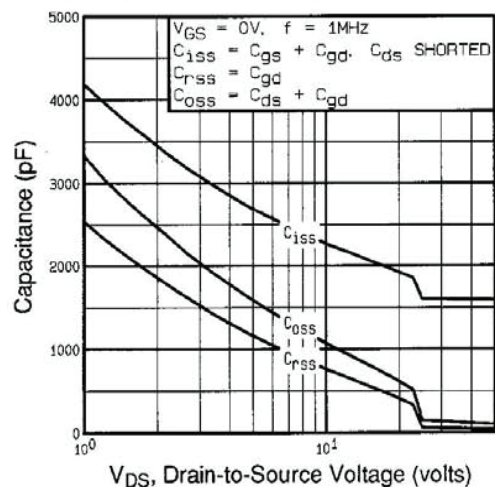


Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage

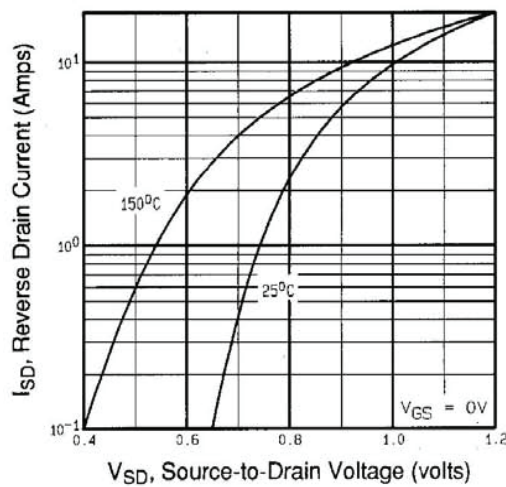


Fig. 7 - Typical Source-Drain Diode Forward Voltage

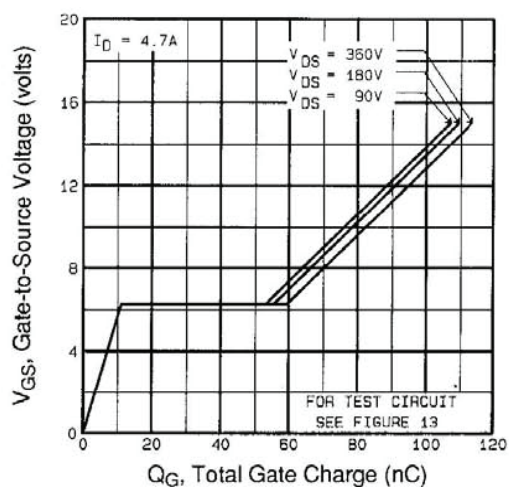


Fig. 6 - Typical Gate Charge vs. Gate-to-Source Voltage

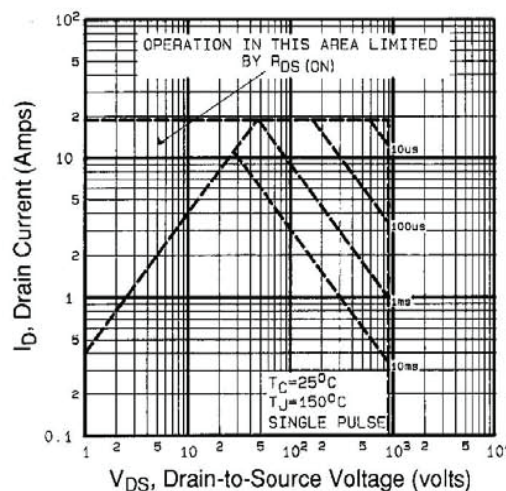


Fig. 8 - Maximum Safe Operating Area

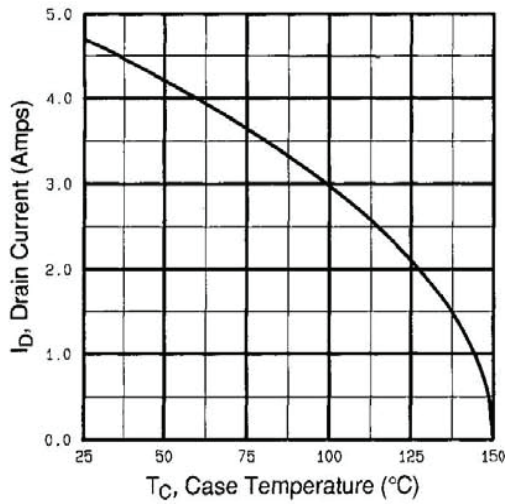


Fig. 9 - Maximum Drain Current vs. Case Temperature

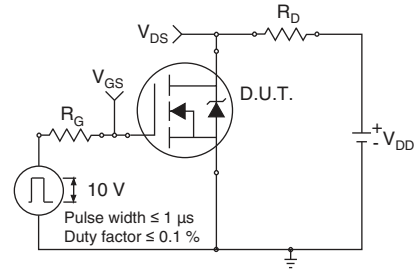


Fig. 10a - Switching Time Test Circuit

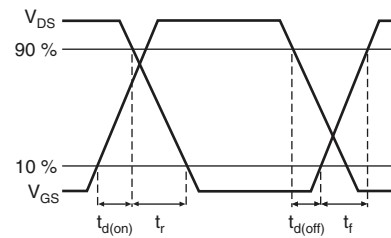


Fig. 10b - Switching Time Waveforms

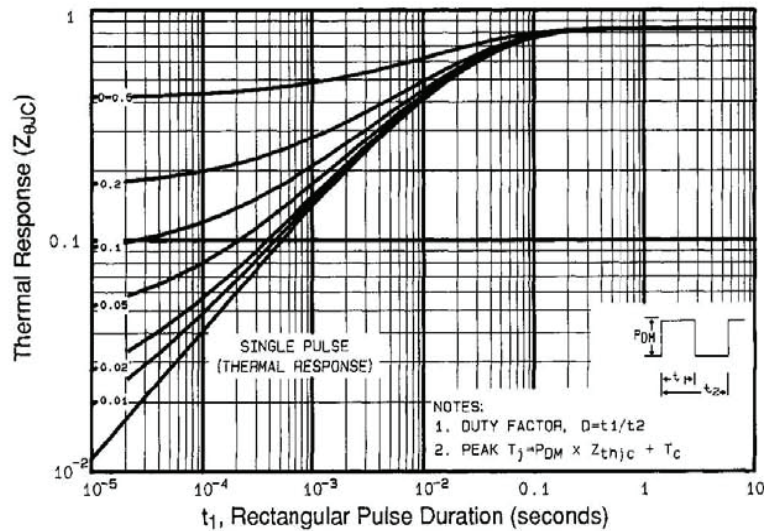


Fig. 11 - Maximum Effective Transient Thermal Impedance, Junction-to-Case

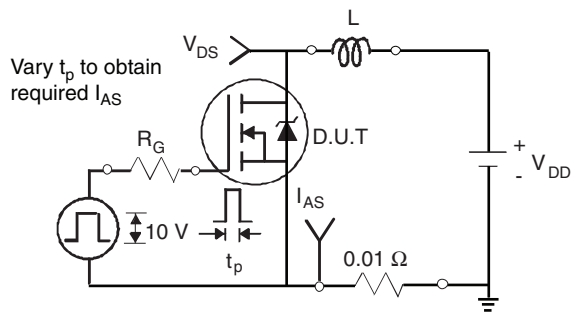


Fig. 12a - Unclamped Inductive Test Circuit

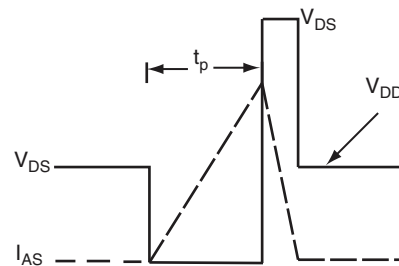


Fig. 12b - Unclamped Inductive Waveforms

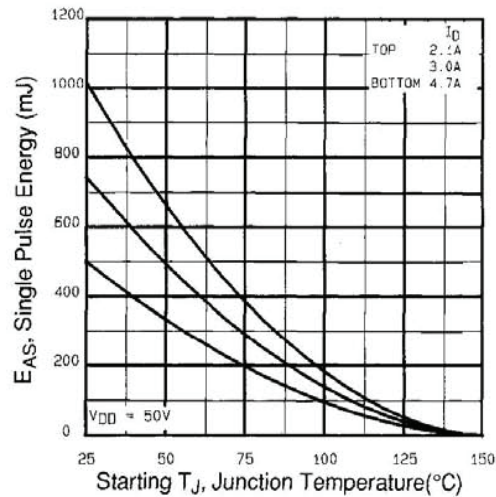


Fig. 12c - Maximum Avalanche Energy vs. Drain Current

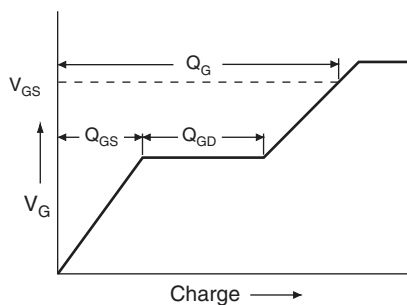


Fig. 13a - Basic Gate Charge Waveform

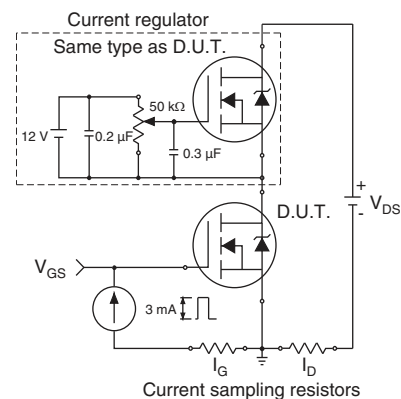
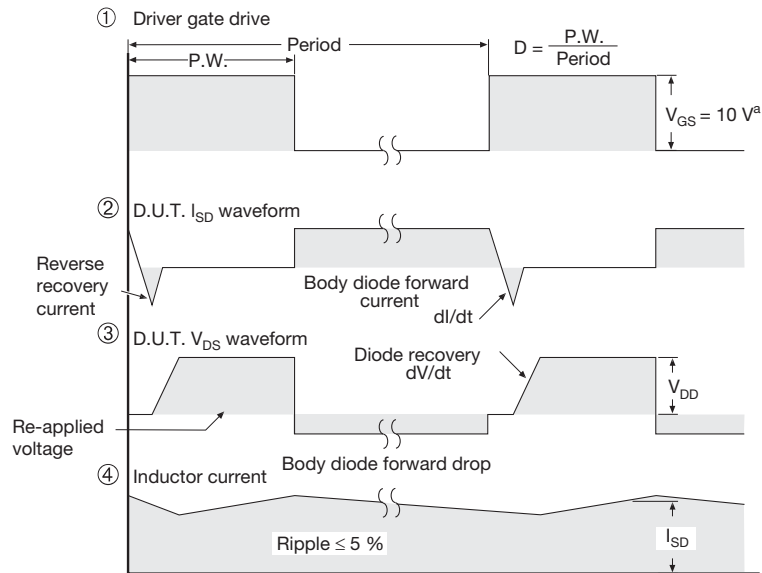
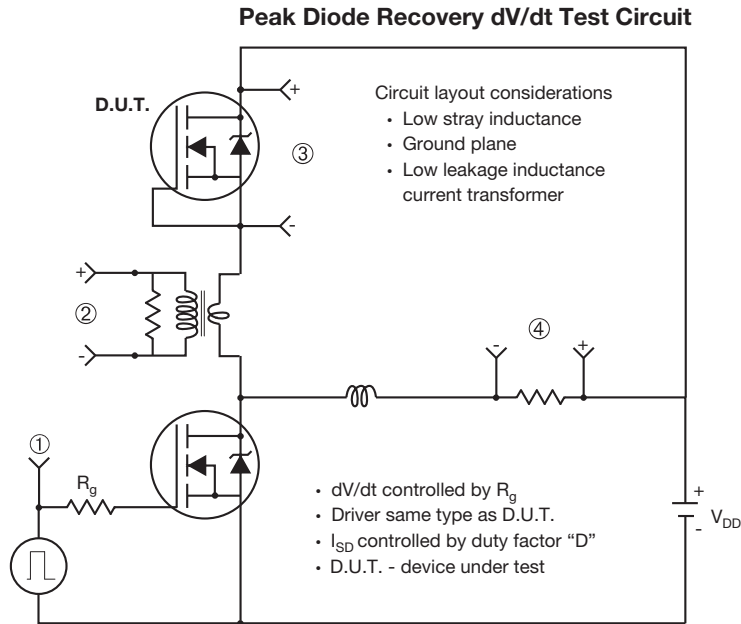


Fig. 13b - Gate Charge Test Circuit



Note

a. $V_{GS} = 5 V$ for logic level devices

Fig. 14 - For N-Channel

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